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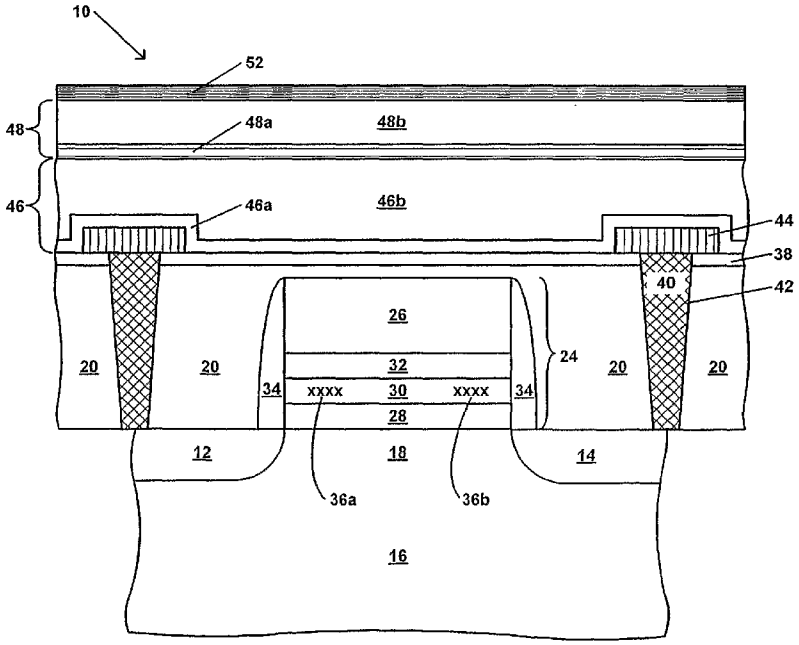
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(54) Title: UV-BLOCKING LAYER FOR REDUCING UV-INDUCED CHARGING OF SONOS DUAL-BIT FLASH MEMORY DEVICES IN BEOL PROCESSING



(57) Abstract: A method of protecting a SONOS flash memory cell (24) from UV-induced charging, including fabricating a SONOS flash memory cell (24) in a semiconductor device (10, 50); and depositing over the SONOS flash memory cell (24) at least one UV-protective layer (38, 46, 48 or 52), the UV-protective layer including a substantially UV-opaque material. A SONOS flash memory device (10, 50), including a SONOS flash memory cell (24); and at least one UV-protective layer (38, 46, 48 or 52), in which the UV-protective layer comprises a substantially UV-opaque material, is provided.

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